

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-1	

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2	kV

ELECTRICAL CHARACTERISTICS($T_j=25$ unless otherwise specified)

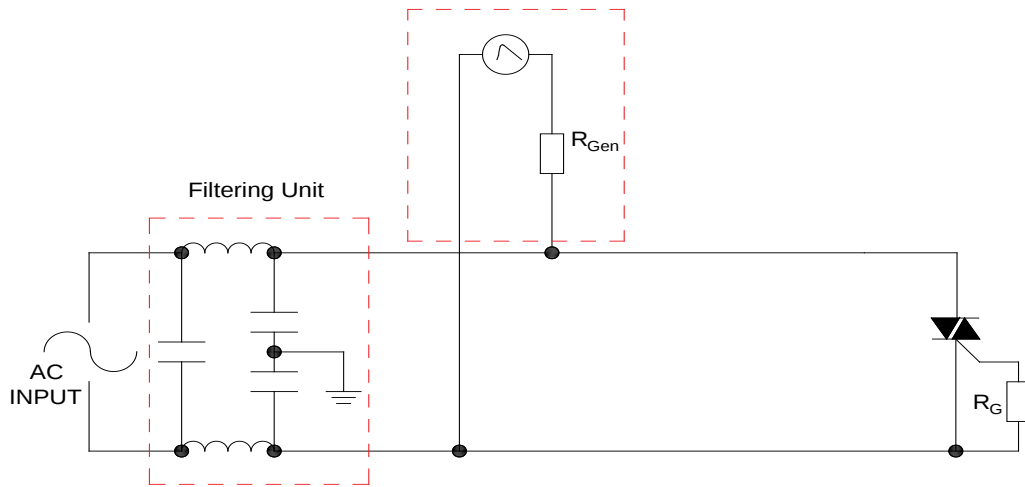
Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V

I_L I_{G-N}

ORDERING INFORMATION

J	ST	60	Z	-800	BW
JieJie Microelectronics Co., Ltd.	Triacs	$I_T(RMS):60A$	$Z:TO-3P(Ins)$	$800:V_{DRM}/V_{RRM} \geq 800V$	$BW:I_{GT1-3} \leq 50mA$

JST60Z-800BW

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standardsIEC61000-4-5 Standards
Surge Generator

LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST60Z-800BW	800	50	TO-3P(Ins)	30	Tube

Document Revision History

Date	Revision	Changes
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Apr.

PACKAGE MECHANICAL DATA



